


EE-SX1055

Miniature Transmissive
Photomicrosensor has 3.6 mm Lead
Length for 1.6 mm PCB thickness

- Physically and electrically identical to EE-SX1025 except with longer leads.
- Infrared LED and phototransistor assure long life and high reliability.
- Narrow aperture slit (0.5 mm) assures high resolution sensing.
- Compact size ideal for applications with restricted space.



Ordering Information

Appearance	Sensing Method	Slot Width	Sensing Object	Output Configuration	Weight	Part Number
	Transmissive	2.8 mm	Opaque, 0.5 x 1.5 mm min.	Phototransistor	Approx. 0.2 g	EE-SX1055

Specifications

■ ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Item		Symbol	Rated Value
Emitter	Continuous Forward current	I_F	50 mA*
	Pulse Forward current	I_{FP}	1 A (frequency: 100 Hz; pulse width: 10 μs)
	Reverse voltage	V_R	4 V
Detector	Collector-emitter voltage	V_{CEO}	30 V
	Collector current	I_C	20 mA
	Collector power dissipation*	P_C	100 mW
Ambient temperature	Operating temperature**	T_{opr}	-25° to 85°C
	Storage temperature	T_{stg}	-30° to 100°C
	Soldering temperature	T_{sol}	260°C at 10 seconds max.

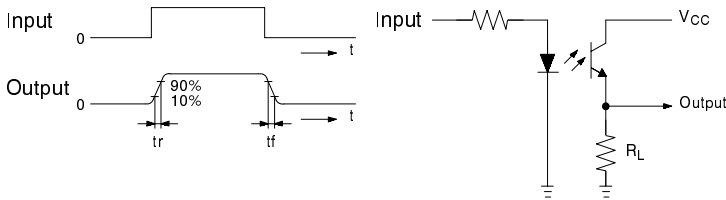
*Continuous forward current (I_F) and collector power dissipation (P_C) must be derated complying with the temperature characteristics shown in Engineering Data.

**The product must be used in applications where neither freezing nor condensation takes place.

CHARACTERISTICS (T_A = 25°C)

Item		Symbol	EE-SX1055	
			Value	Condition
Emitter	Forward voltage	V _F	1.2 V typ. 1.5 V max.	I _F = 30 mA
	Reverse current	I _R	0.01 μA typ. 10 μA max.	V _R = 4 V
	Peak emission wavelength	λ _p (L)	940 nm typ.	I _F = 20 mA
Detector	Dark current	I _D	2 nA typ. 200 nA max.	V _{CE} = 10 V 0/x
	Peak spectral sensitivity wavelength	λ _p (P)	850 nm typ.	V _{CE} = 10 V
Combination	Light current (collector current)	I _L	0.5 mA min. 14 mA max.	I _F = 20 mA V _{CE} = 10 V
	Collector-emitter saturated voltage	V _{CE} (sat)	0.1 V typ. 0.4 V max.	I _F = 20 mA I _L = 0.1 mA
	Rising time (see note)	t _r	4 μs typ.	V _{CC} = 5 V R _L = 100 Ω
	Falling time (see note)	t _f	4 μs typ.	I _L = 5 mA

Note: The following illustrations show the rising time, t_r, and the falling time, t_f.

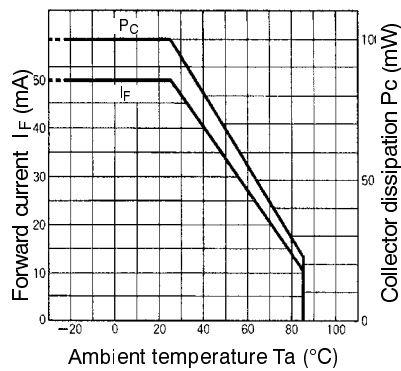


Engineering Data

Note: The operating conditions of the photomicrosensor must be within the absolute maximum rating ranges.

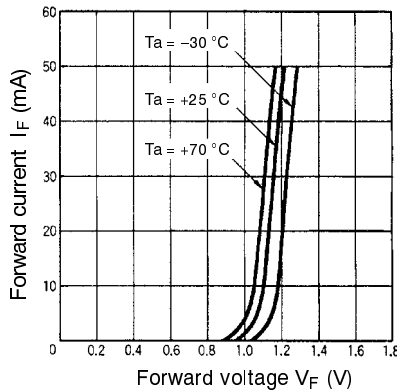
TEMPERATURE CHARACTERISTICS

EE-SX1055



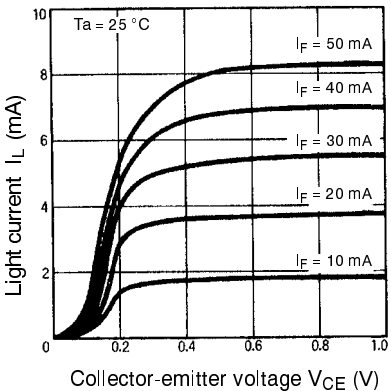
INPUT CHARACTERISTICS (TYPICAL)

EE-SX1055



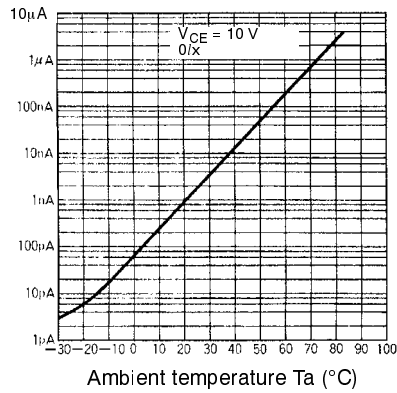
OUTPUT CHARACTERISTICS (TYPICAL)

EE-SX1055



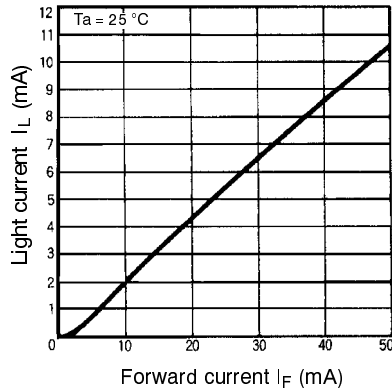
■ DARK CURRENT TEMPERATURE DEPENDENCY (TYPICAL)

EE-SX1055



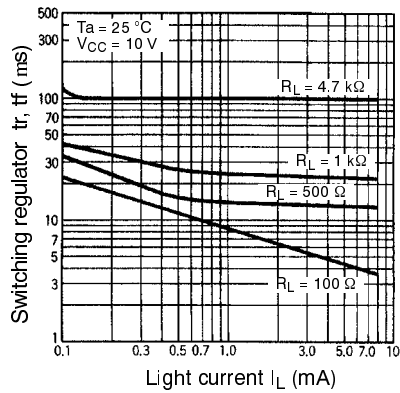
■ I/O CHARACTERISTICS (TYPICAL)

EE-SX1055



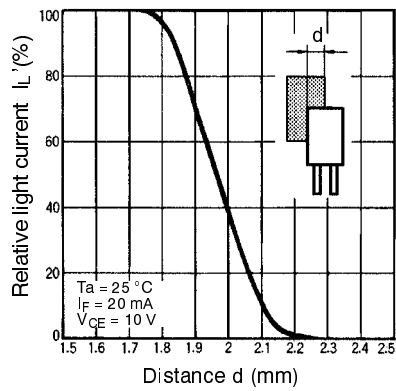
■ SWITCHING CHARACTERISTICS (TYPICAL)

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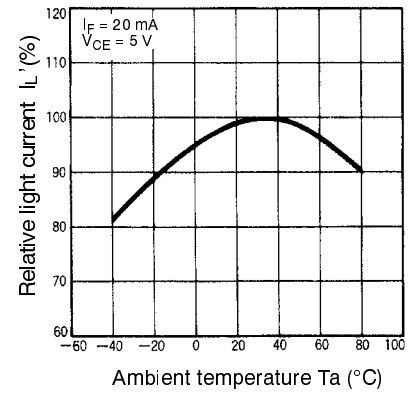
■ SENSING POSITION CHARACTERISTICS (TYPICAL)

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■ LIGHT CURRENT TEMPERATURE DEPENDENCY (TYPICAL)

EE-SX1055



NOTE: DIMENSIONS SHOWN ARE IN MILLIMETERS. To convert millimeters to inches divide by 25.4.

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